

Mid Infrared Absorption Spectroscopy System for Plasma Monitoring

Q-MACS Team

in cooperation with INP Greifswald

2009

www.neoplas-control.de

Introduction

QCLAS Technology

Applications of the Q-MAC System

- Plasmas in Surface Treatment Industry
- Plasmas in Semiconductor Industry
- Q-MACS Multi Component

Quantum-Cascade-Measurement and Control System – Q-MACS®

problem: real-time and in-situ control of plasma processes and trace

gas analysis with a detection limit up to ppt

idea: application of a new class of infrared lasers:

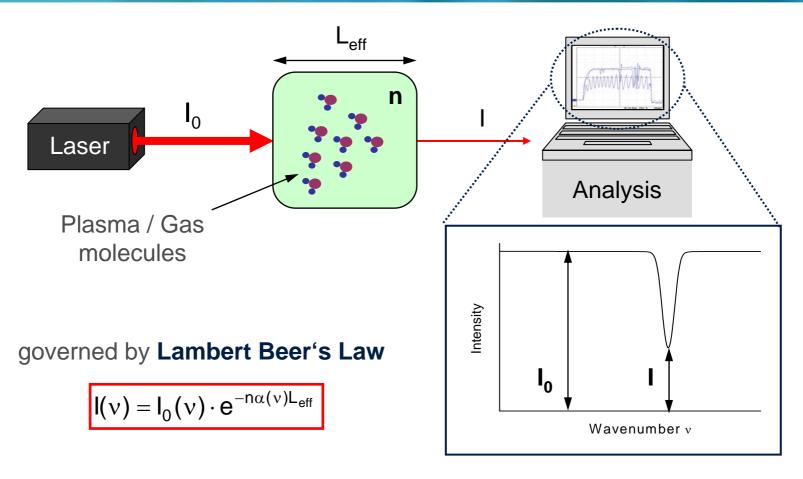
quantum-cascade-laser (QCL)

result: development of compact and easy to use systems for

industrial and scientific applications

Q⋅macs

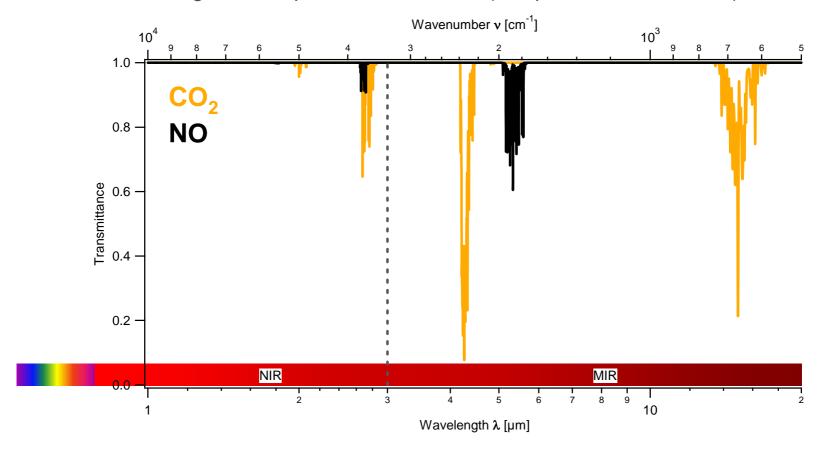
Q-MACS: Quantum Cascade Laser Measuring and Control System



Principle: Absorption of the laser beam by plasma / gas molecules

Result: On-line concentration of molecules

- many molecules ...
 - only detectable in the (3 ... 20) µm spectral range (MIR)
 - with higher absorption cross sections (compared to VIS, NIR, ...)



	IR - TDLAS	<u>IR - QCLAS</u>	CRDS	FT - IR
sensitivity (I ₀ -I)/I ₀	© (10 ⁻³ 10 ⁻⁵)	◎ (10 ⁻³ 10 ⁻⁵)	© (10 ⁻³ 10 ⁻⁵)	⊗ (10 ⁻² 10 ⁻³)
selectivity Δu	© (10 ⁻⁴ 10 ⁻³) cm ⁻¹	© (10 ⁻³ 10 ⁻²) cm ⁻¹	© (10 ⁻⁴ 10 ⁻³) cm ⁻¹	8 0.1 cm ⁻¹
tunability	⊕ (10100) cm ⁻¹	<mark>8</mark> (110) cm ⁻¹	8 (110) cm ⁻¹	[☺] whole MIR
time resolution Δt	⊕ ms (µs)	© ms…ns	😩 sms	8 mins
operation/ detection	⊗ (20 - 130) K⊗ LN₂ detectors	○ near room T○ TE detectors	needs highly reflective mirrorsmirrors selected for single wavelength	© room T © LN ₂ detectors

Q-MACS Technology – wide spread applications

neoplascontrol

Plasma Industry /

Exhaust Gas Treatment /

Environmental Technology



Process Control in Deposition and Etching Reactors

Semiconductor Industry

Car Industry

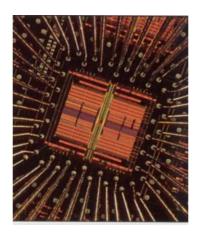
Medicine Technique

Combustion

Fusion Devices

UF₆ enrichment ...





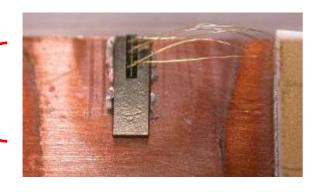




Technology

- quantum cascade laser absorption spectrometer
- identifies gases and plasma species and quantifies their concentrations
- very low detection limits (up to ppt)
- enables in-situ measurements
- very high temporal resolution (real-time, ns ms s)
- works at room temperature

1 cm







Product variants for customized high performance diagnostics

Q-MACS Basic

key component, laser head with control- and supply unit



Q-MACS Process

high sensitive real-time gas and plasma sensing



Q-MACS Trace compact

trace gas detection and environmental monitoring



Q-MACS Process Fibre

measurement and control system for plasma etch systems



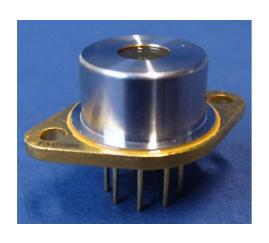
Q-MACS Basic

- key component for all Q-MAC Systems
- for operation with pulsed and cw QCLs
- laser head with control and supply unit for applications in spectroscopy





TO-3 Packaging of QCL in Q-MACS Applications



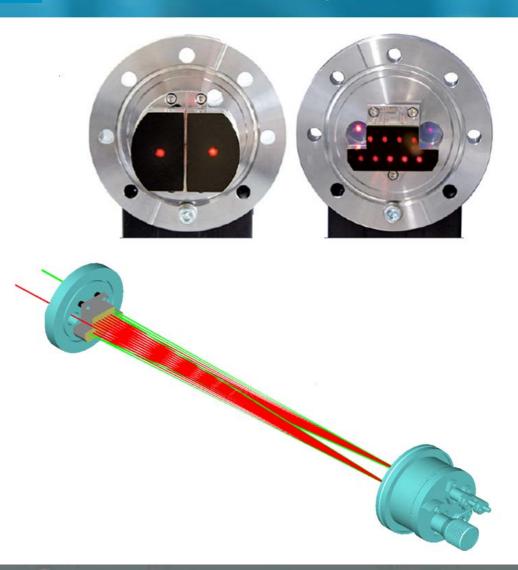


For robust handling in industrial environment

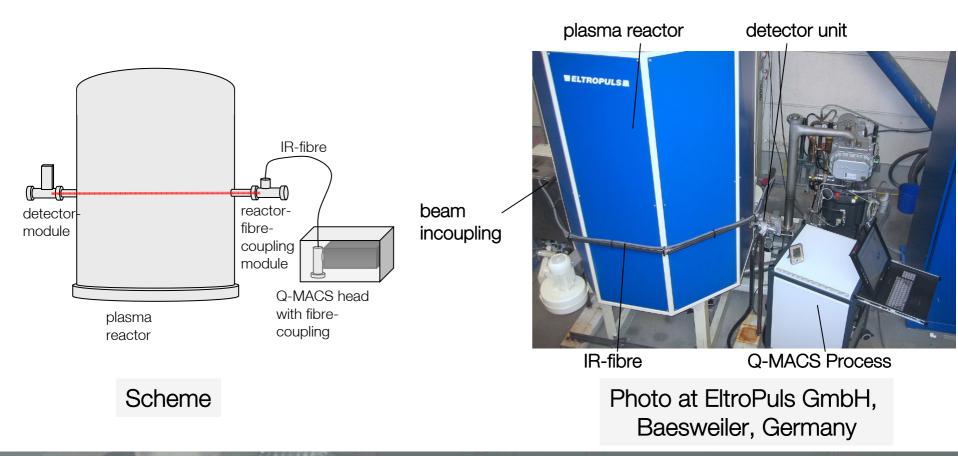
neoplascontrol

Q-MACS Multipass optics

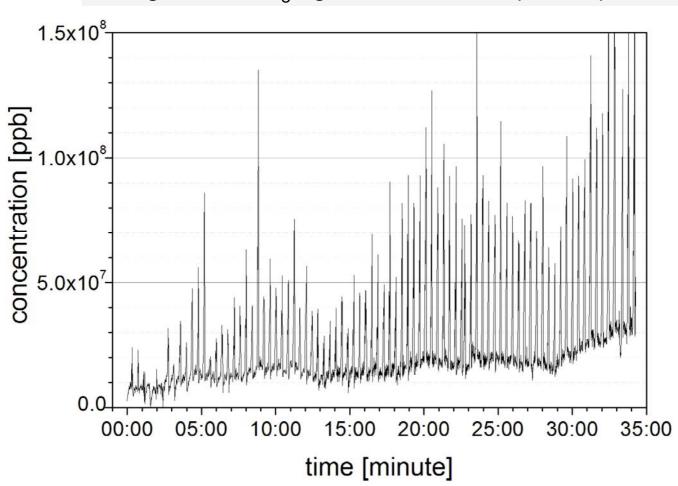
- efficient solution to increase the effective absorption length
- include a robust and compact set of gold coated mirrors
- flange mounted for in-situ installation at plasma chambers
- allow a wide range of possible absorption lengths



Q-MACS Process with IR-fibre coupled to the industrial plasma reactor for surface treatment

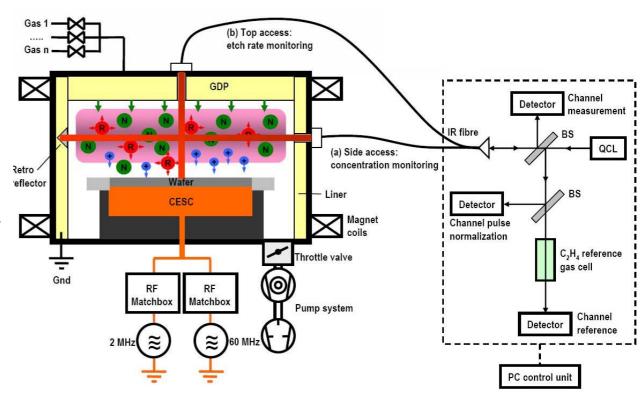


Change of the BCl₃ signal in an industrial plasma process



Q-MACS Process Fibre - concept

- optical coupling of the radiation at the process chamber via IR fiber
- reflective elements in-situ (mirror, wafer) for detecting via single view port
- optic board with multi channels for referencing the laser emission



Q-MACS Process Fibre

Development objectives

- monitoring of species concentration relevant for silicon plasma etch processes via Quantum Cascade Laser Measuring and Control System (Q-MACS)
- adaptation of Q-MACS for in-situ application at process tools with single access (one window)
- process control via IR laser absorption spectroscopy
- monitoring of the etch progress via online depth control measurements

Q-MACS Process Fibre

- realization of a tool for in-situ monitoring of silicon plasma etching
- development and design of a compact and integrable product
- process control with Q-MAC System possible
- enables strong improvements in process stability and reproducibility





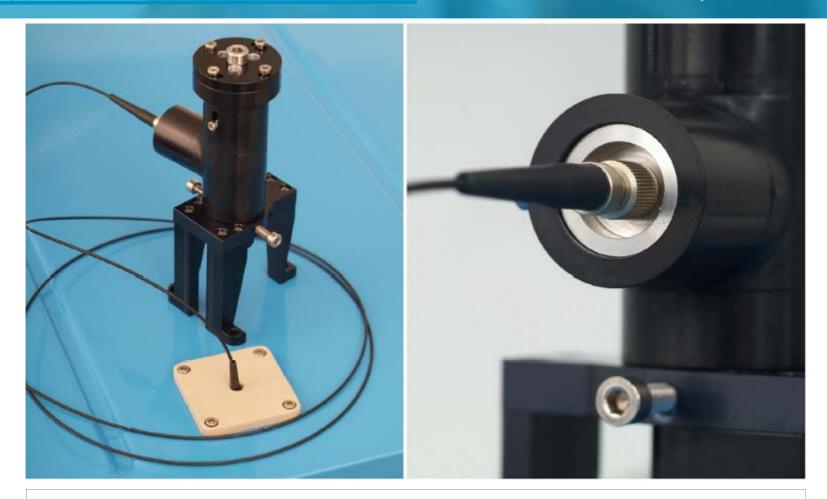
at a HART III plasma etch system

neoplascontrol



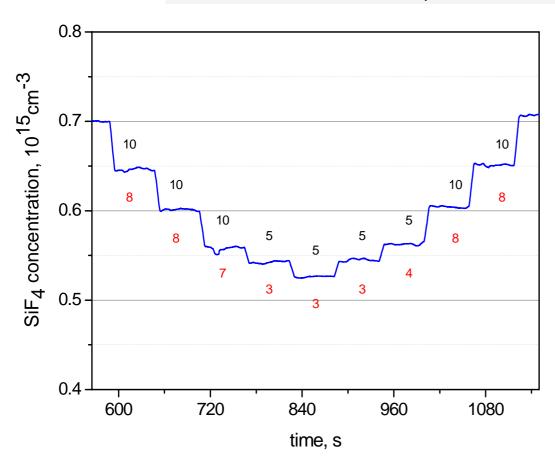
Q-MACS Process fibre - 2008 edition (overall view) control unit - optical unit - process coupling unit with IR fibre

neoplascontrol



Q-MACS Process fibre - 2008 edition process coupling unit with IR fibre

Q-MACS Process Fibre - Dilution of SiF_4 with Ar p=50 mTorr, SiF_4 flow = 200 sccm



black numbers:

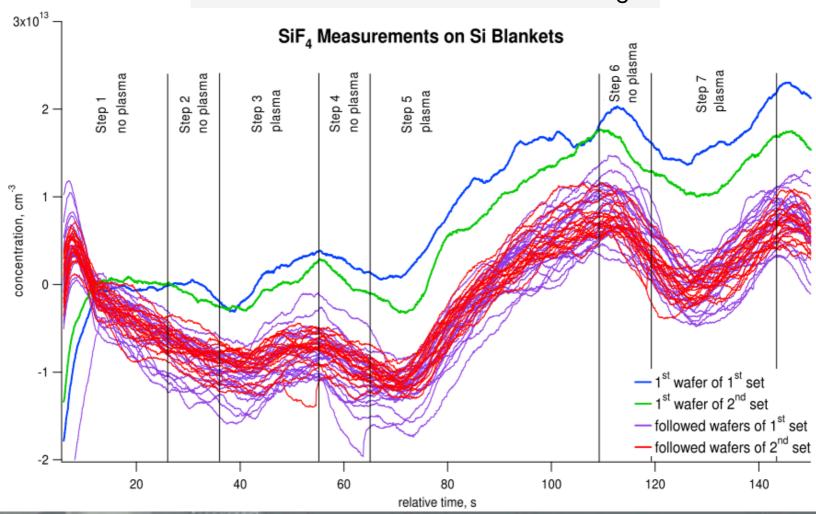
% step size of Ar-MFC-FSR

FSR: 400 sccm

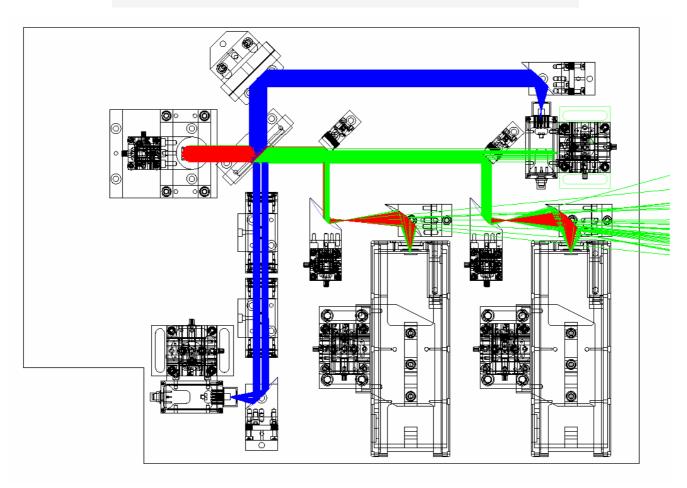
red numbers:

% change of Ar concentration

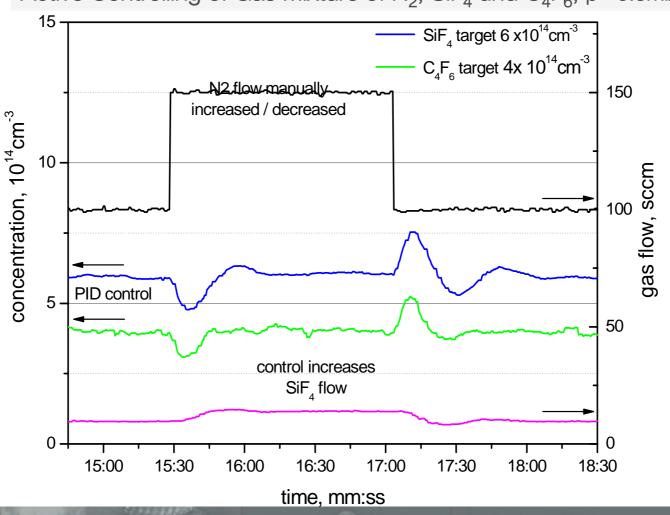
Q-MACS Process Fibre – etch monitoring



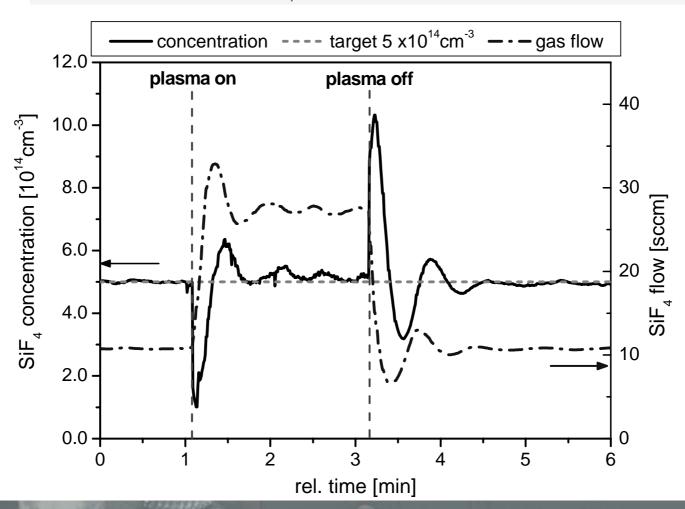
Q-MACS Process Fibre with 2 QCL Heads



Active Controlling of Gas Mixture of N₂, SiF₄ und C₄F₆, p= 0.3mbar

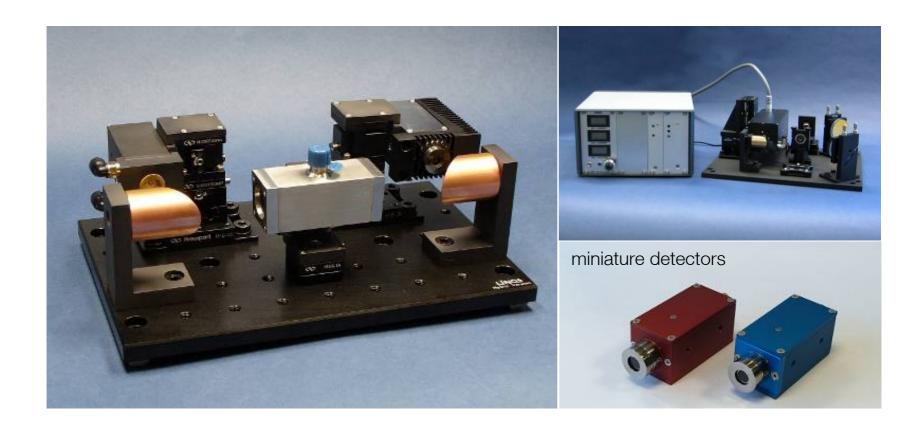


Active Controlling of SiF₄ Concentration in Plasma Reactor, p= 0.3 mbar



neoplascontrol

Examples of optimized and compact Q-MAC Systems



Principle of QCLAS

Q-MACS Technology

Applications of the Q-MAC System

- Surface Treatment Industry *time resolved in-situ species monitoring*
- Semiconductor Industry process monitoring
- Q-MACS Multi Component multiple species monitoring, MFC calibration
- CxHy, CO, CO₂, NO, NO₂, N₂O, NH₃, NF₃, BCl₃, B₂H₆, SiF₄, C₄F₆, COCl₂, PH₃, H₂O, O₃, SO₂, OH, HF, HCl, OCS, HCN, COF₂, H₂O₂, SF₆, SO₃, HNO₃, CH₃CL, H₂CO, CH₃OH and many others